

Silicon NPN transistor epitaxial type

D5930

[Applications]

Inverter, Strobo flash, DC-DC convertor

with high current, high DC current gain and small collector-emitter saturation voltage.

High power switching with high collector current.

[Feature]

Small collector-emitter saturation voltage VCE(sat)= 0.28V(Typ.) at IC= 3A,IB= 0.1A

High collector current IC= 5A

High emitter-base breakdown voltage BVEBO= 9V

High DC current gain hFE= 355-800

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	20	V
Collector-emitter voltage	VCEO	12	V
Emitter-base voltage	VEBO	9	V
Collector current	IC	5	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	20	-	-	V	IC= 10uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	12	-	-	V	IC= 1mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	9	-	-	V	IE= 10uA, IC= 0A
Collector cut-off current	ICBO	-	-	100	nA	VCB= 10V, IE= 0A
Collector cut-off current	ICEO	-	-	1	uA	VCE= 10V, IE= 0A
Emitter cut-off current	IEBO	-	-	100	nA	VEB= 7V, IE= 0A
DC current gain 1	hFE 1	355	-	800	-	VCE= 2V, IC= 0.5A
DC current gain 2	hFE 2	150	-	-	-	VCE= 2V, IC= 2A
Collector-emitter saturation voltage	VCE(sat)	-	0.28	0.8	V	IC= 3A, IB= 0.1A
Transition frequency	f T	-	150	-	MHz	VCE= 6V, IE= -50mA
Collector output capacitance	Cob	-	-	50	pF	VCB= 10V, f = 1MHz, IE= 0A

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

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